

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI TVV005 is Designed for

FEATURES:

-
-
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CB0}	55 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	50 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	3.5 °C/W

PACKAGE STYLE .280 4L STUD

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10654

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	30			V
BV_{CER}	I _C = 20 mA R _{BE} = 10 Ω	55			V
BV_{CB0}	I _C = 20 mA	55			V
BV_{EBO}	I _E = 2.0 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	10		---	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			35	pF
P_G	V _{CE} = 28 V P _{OUT} = 5.0 W I _C = 1.0 A f = 225 MHz	15			dB
IMD₁	V _{CE} = 28 V P _{OUT} = 5.0 W I _C = 1.0 A f = 225 MHz Vision Carrier = -8 dB ref. Sound Carrier = -7 dB ref. Sideband Signal = -16 dB ref.	-55			dBc
ψ	V _{CE} = 28 V P _{OUT} = 5.0 W I _C = 1.0 A f = 225 MHz Load VSWR = ∞:1, All Phase Angles	No Degradation in Output Power			